

Supporting Information (SI)

Achieving high energy density for lithium-ion battery anodes by Si/C nanostructures design

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Table S1 Comparison of lattice constants of $g\text{-SiC}_2$ and $g\text{-SiC}_3$ with previous theoretical results. “–” represents that there is no corresponding result for $g\text{-SiC}_2$ or $g\text{-SiC}_3$. The unit is Å.

	This work	Ref. 35	Ref. 36
$g\text{-SiC}_2$	5.02	5.019	–
$g\text{-SiC}_3$	5.62	–	5.633

Table S2 Adsorption energies on various possible adsorption sites. The most stable adsorption sites are highlighted in red. For C1 sites of $g\text{-SiC}_2$ and $g\text{-SiC}_3$, Li atoms will move to C2 and H1 sites after the optimization, respectively. The unit is eV.

	C1	C2	Si	H	H1	H2
$g\text{-SiC}_2$	-1.71 (C2)	-1.71	-1.25	-2.14	–	–
$g\text{-SiC}_3$	-2.24 (H1)	–	-1.54	–	-2.24	-1.95

Table S3 Adsorption energies at different Li coverages. The unit is eV.

	1×1	2×1	2×2	3×2	3×3
$g\text{-SiC}_2$	-2.14	-2.21	-2.25	-2.27	-2.28
$g\text{-SiC}_3$	-2.24	-2.28	-2.33	-2.35	-2.35

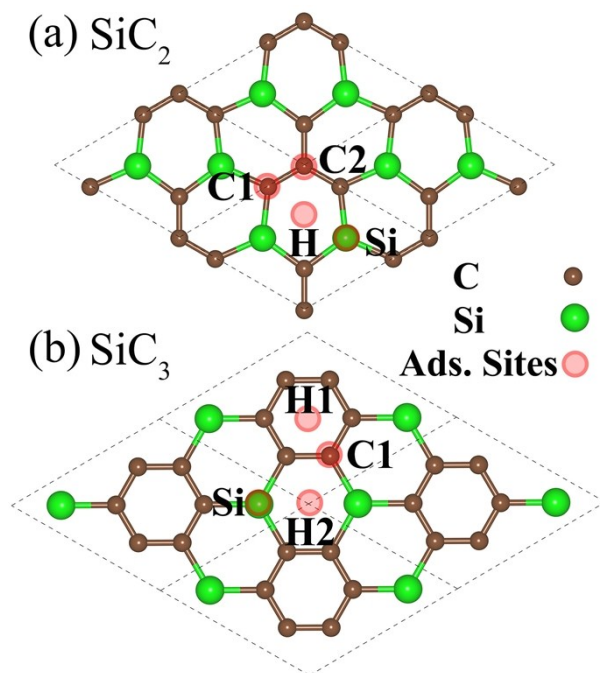


Figure S1 Schematic representations of the (2×2) supercells of (a) $g\text{-SiC}_2$ and (b) $g\text{-SiC}_3$. Small (Brown) and large (green) balls represent carbon and Si atoms, respectively.

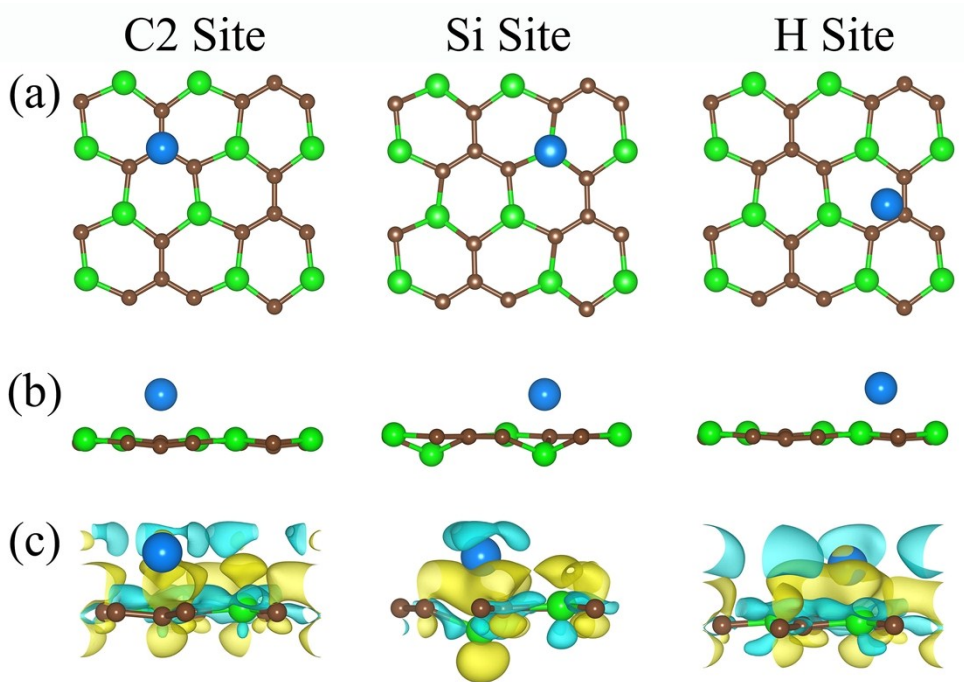


Figure S2 (a) Top and (b) side views of three high-symmetry Li adsorption sites (C2, Si and H sites) on g-SiC₂. (c) Corresponding difference charge density. The yellow and blue areas represent electron gains and losses. The difference charge density ($\Delta\rho$) is calculated by $\Delta\rho = \rho_{total} - \rho_{SG} - \rho_{Li}$, where ρ_{total} , ρ_{SG} and ρ_{Li} are the total charge of the system, siligraphene and lithium atom, respectively.

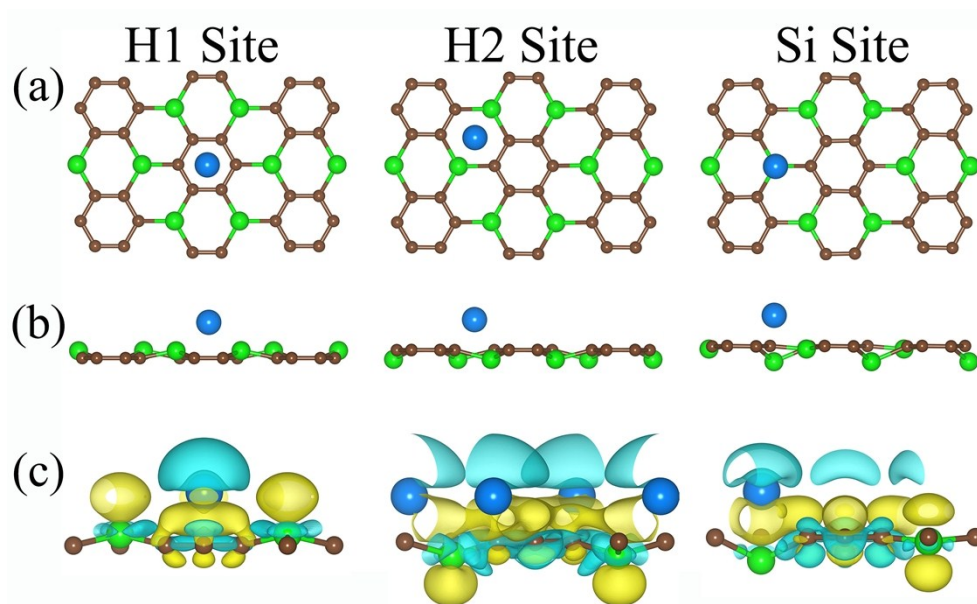


Figure S3 (a) Top and (b) side views of three high-symmetry Li adsorption sites (C2, Si and H sites) on $g\text{-SiC}_3$. (c) Corresponding difference charge density.

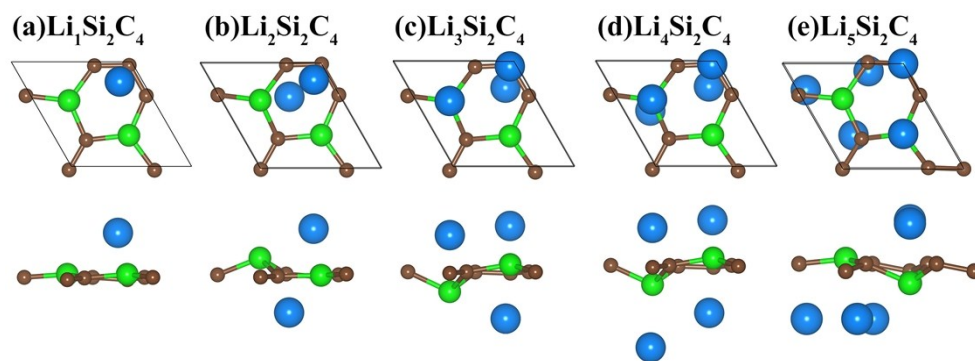


Figure S4 The most stable configurations of different n ($n = 1, 2, 3, 4$ and 5) of $\text{Li}_n\text{Si}_2\text{C}_4$.

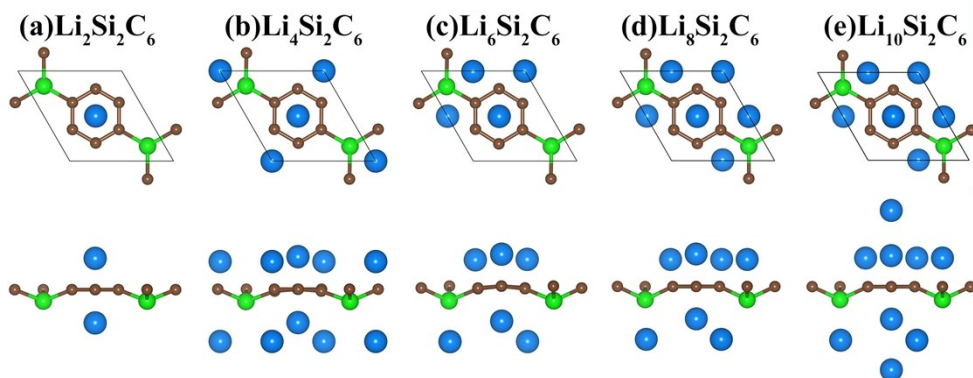


Figure S5 The most stable configurations of different n ($n = 2, 4, 6, 8$ and 10) of $\text{Li}_x\text{Si}_2\text{C}_6$.

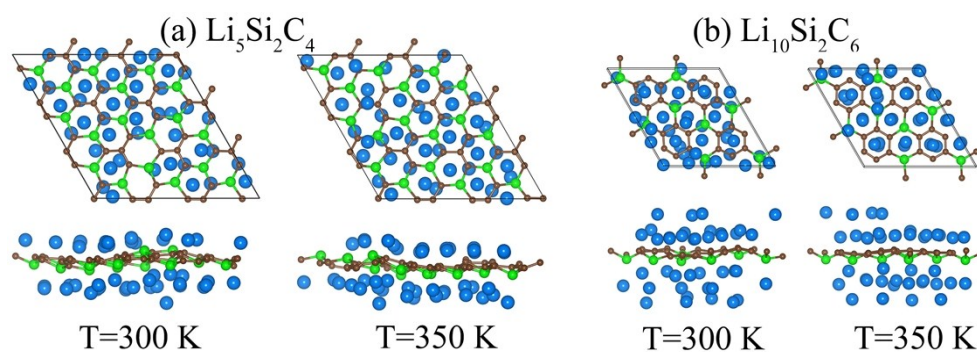


Figure S6 Snapshots of the final configurations of (a) $\text{Li}_5\text{Si}_2\text{C}_4$ and (b) $\text{Li}_{10}\text{Si}_2\text{C}_6$ at temperatures of 300 and 350 K at the end of 10 ps AIMD simulations.

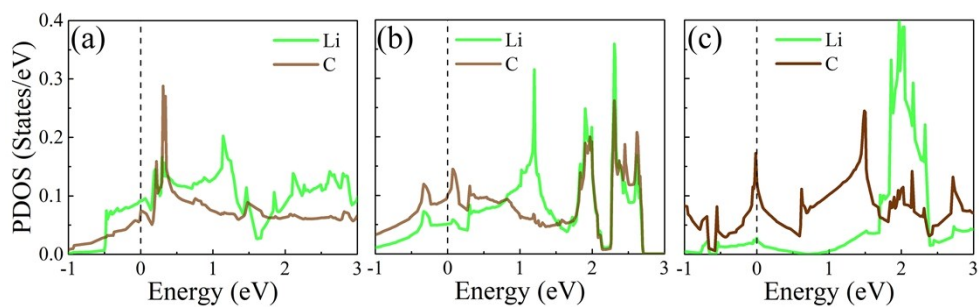


Figure S7 Projected density of states (PDOS) of Li adsorption on (a) graphene, (b) *g*-SiC₂ and (c) *g*-SiC₃. The Fermi level is set to zero.

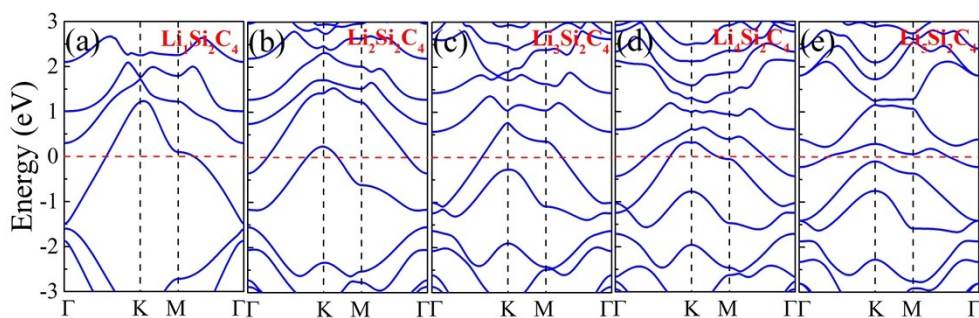


Figure S8 Band structures of (a) Li₁Si₂C₄, (b) Li₂Si₂C₄, (c) Li₃Si₂C₄, (d) Li₄Si₂C₄ and (e) Li₅Si₂C₄, respectively. The Fermi level is set to zero.

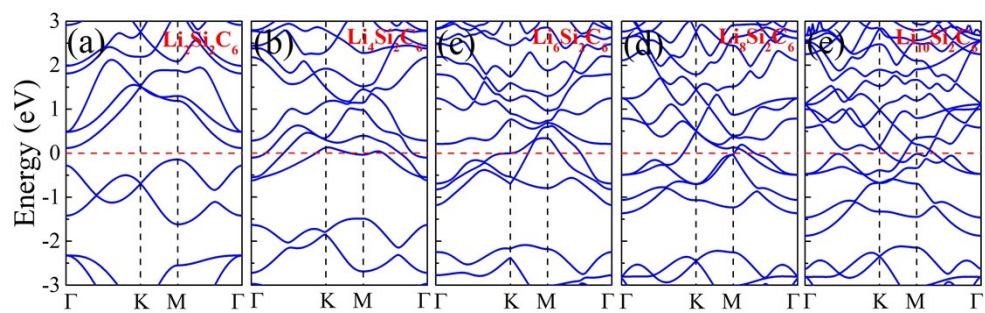


Figure S9 Band structures of (a) $\text{Li}_2\text{Si}_2\text{C}_6$, (b) $\text{Li}_4\text{Si}_2\text{C}_6$, (c) $\text{Li}_6\text{Si}_2\text{C}_6$, (d) $\text{Li}_8\text{Si}_2\text{C}_6$ and (e) $\text{Li}_{10}\text{Si}_2\text{C}_6$, respectively. The Fermi level is set to zero.